***Supporting Information for***

# Elemental Quantitative Imaging Analysis of $Bi_4Si_3O_{12}$ Crystals Defects by LA-ICP-MS

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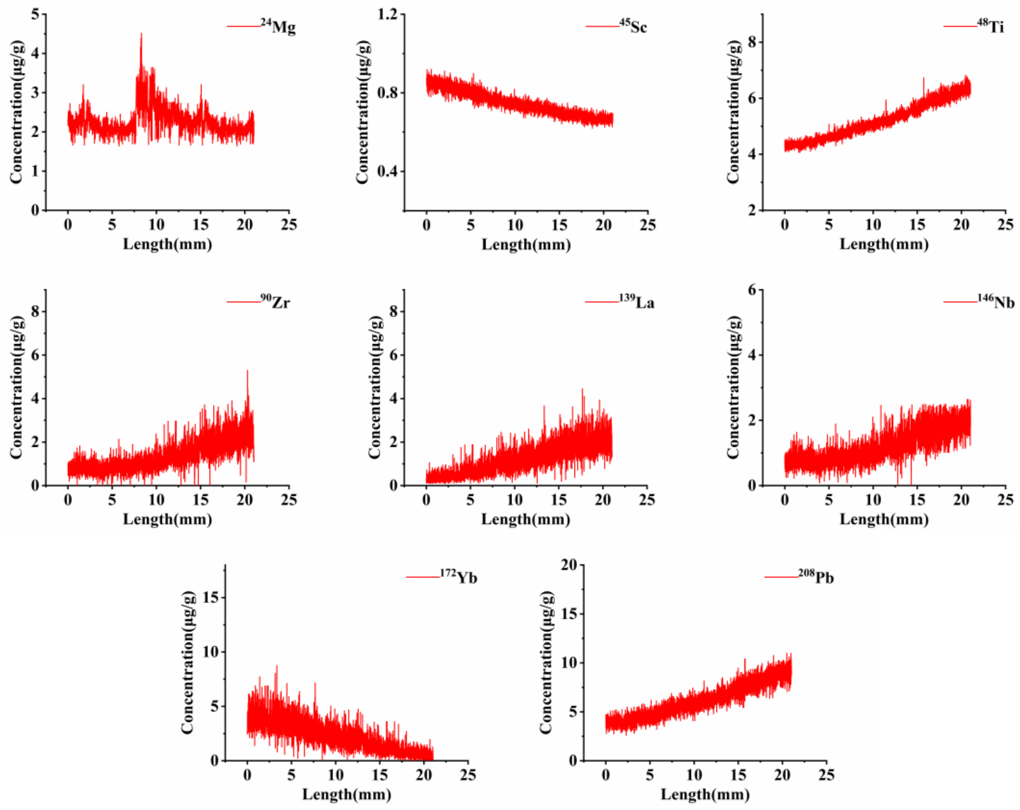


**Fig. S1**. Distribution of impurity elements in the axial direction of the $Bi_4Si_3O_{12}$ crystal.